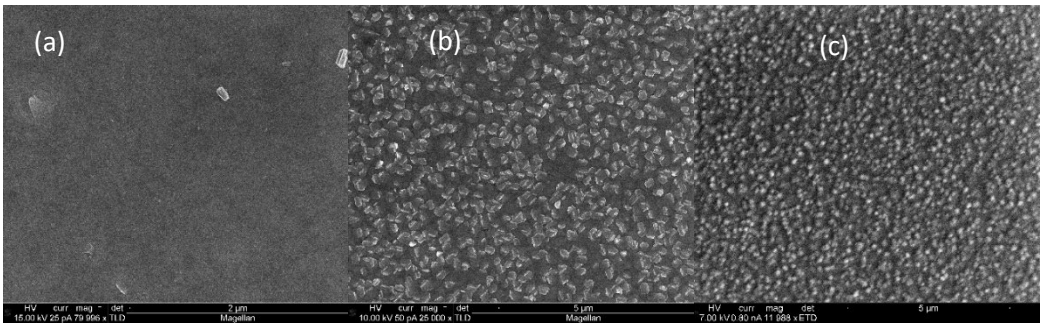

Fig. 1 SEM images of $Ge_{0.84}In_{0.16}Te$ (a), $Ge_{0.81}In_{0.19}Te$ (b) and $Ge_{0.60}In_{0.40}Te$ (c) films.

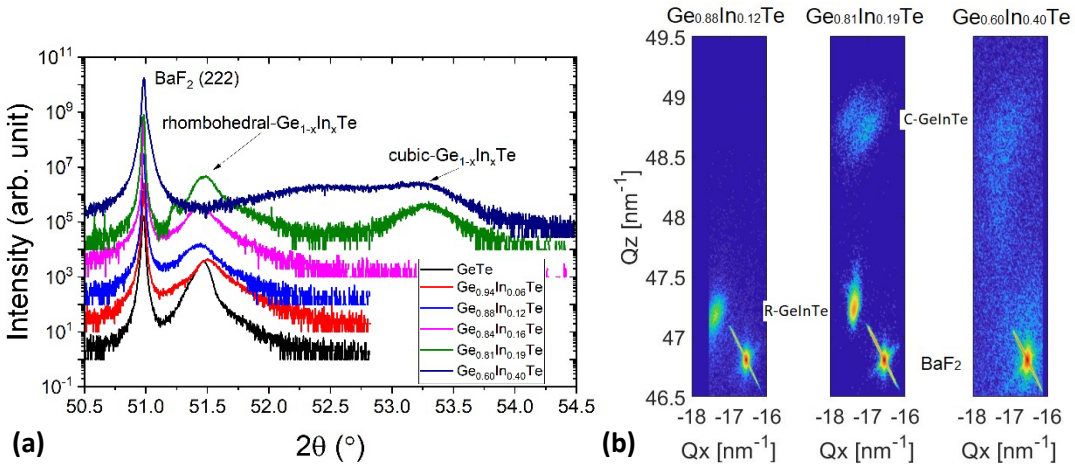

Fig. 2 (a) XRD ω–2θ scan along the (222) plane of BaF_2 substrates for a series of GeInTe films. (b) RSMs around the asymmetric BaF_2(224) Bragg peaks with $Q_z \| BaF_2[111]$ and $Q_x \| BaF_2[11\text{-}2]$.

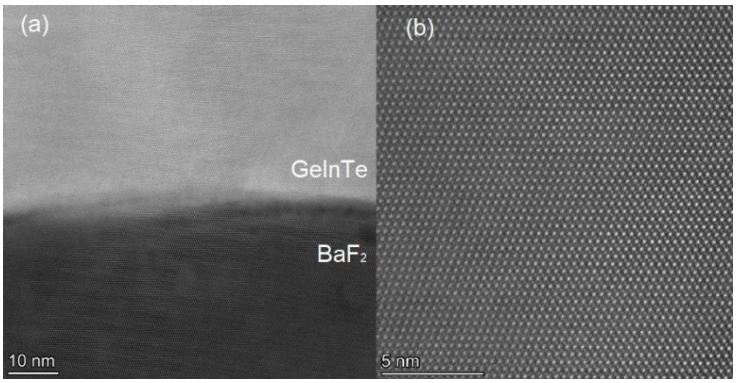

Fig. 3 (a) TEM images of a GeInTe/BaF_2(111) interface. (b) HRTEM image of a GeInTe lattice.

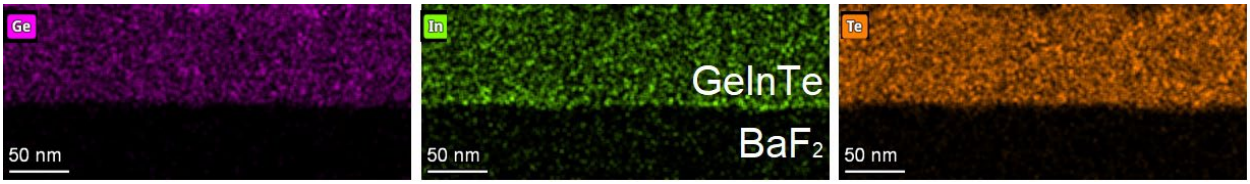

Fig. 4 Energy dispersive X-ray (EDX) mapping analysis of composites at GeInTe/BaF_2(111) interface.

References

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